

GENERAL DESCRIPTION

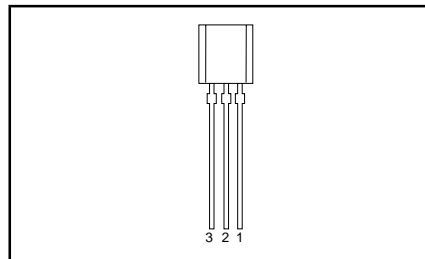
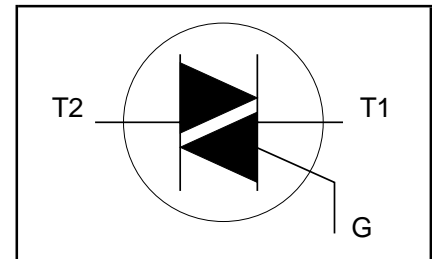
Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V_{DRM}	BT131- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	600	800	V
$I_{T(RMS)}$		600	800	
I_{TSM}		1	1	A
		16	16	A

PINNING - TO92

PIN	DESCRIPTION
1	main terminal 2
2	gate
3	main terminal 1

PIN CONFIGURATION

SYMBOL

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				-600 600 ¹	-800 800 ¹	
V_{DRM}	Repetitive peak off-state voltages		-	-600 600 ¹	-800 800 ¹	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 51^\circ C$	-	1		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ C$ prior to surge $t = 20$ ms	-	16		A
		$t = 16.7$ ms	-	17.6		A
I^2t	I^2t for fusing	$t = 10$ ms	-	1.28		A ² s
di_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 1.5$ A; $I_G = 0.2$ A; $di_G/dt = 0.2$ A/ μ s	-	50		A/ μ s
		T2+ G+	-	50		A/ μ s
		T2+ G-	-	50		A/ μ s
		T2- G-	-	50		A/ μ s
		T2- G+	-	10		A/ μ s
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5		W
T_{stg}	Storage temperature		-40	150		$^\circ C$
T_j	Operating junction temperature		-	125		$^\circ C$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/ μ s.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-lead}$	Thermal resistance junction to lead	full cycle	-	-	60	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle pcb mounted; lead length = 4mm	-	-	80	K/W
			-	150	-	K/W

STATIC CHARACTERISTICS
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$				
		T2+ G+	-	0.4	3	mA
		T2+ G-	-	1.3	3	mA
		T2- G-	-	1.4	3	mA
		T2- G+	-	3.8	7	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$				
		T2+ G+	-	1.2	5	mA
		T2+ G-	-	4.0	8	mA
		T2- G-	-	1.0	5	mA
		T2- G+	-	2.5	8	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	1.3	5	mA
V_T	On-state voltage	$I_T = 2.0\text{ A}$	-	1.2	1.5	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7	1.5	V
I_D	Off-state leakage current	$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.2	0.3	-	V
		$V_D = V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ exponential waveform; $R_{GK} = 1\text{ k}\Omega$	5	15	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 1.5\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

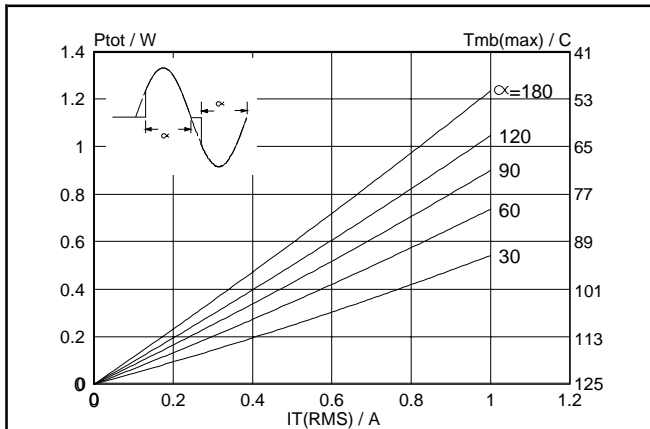


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

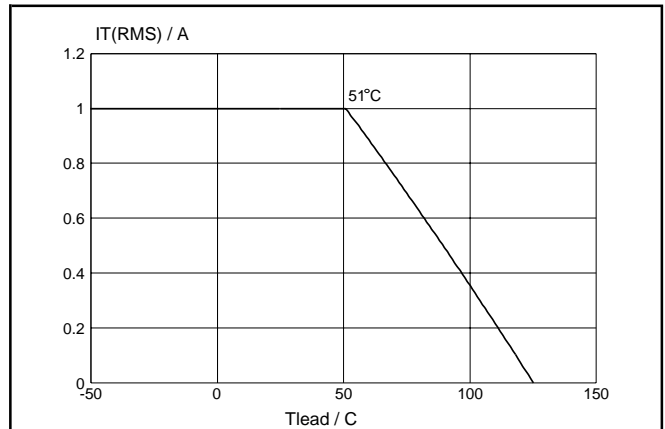


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus lead temperature T_{lead} .

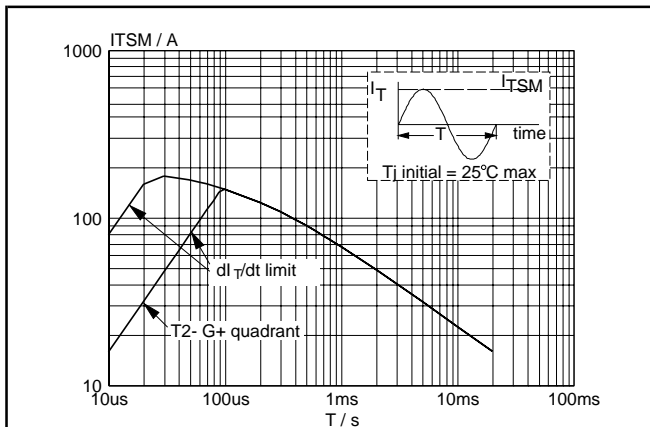


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20\text{ms}$.

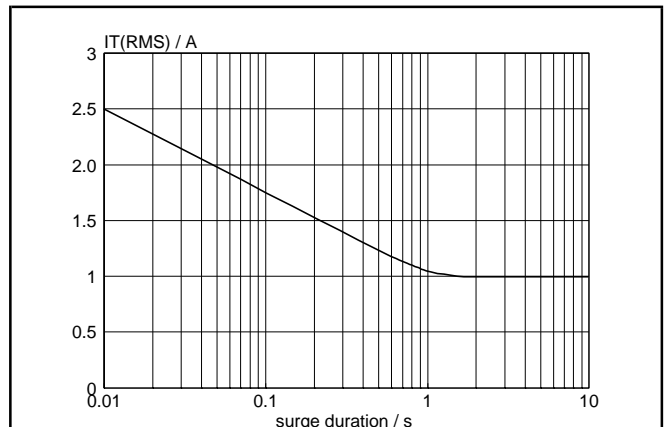


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50\text{ Hz}$; $T_{lead} \leq 51^\circ\text{C}$.

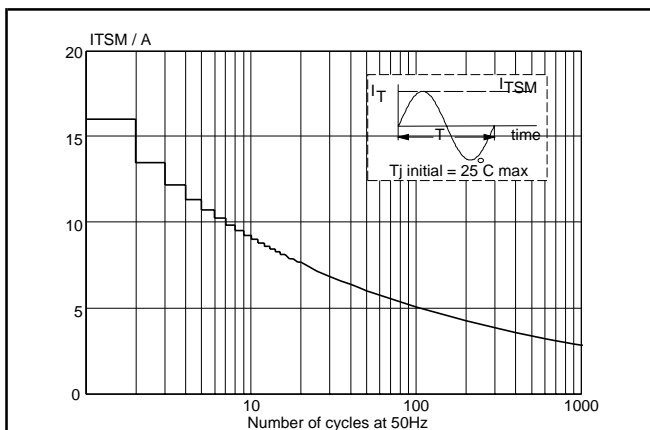


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50\text{ Hz}$.

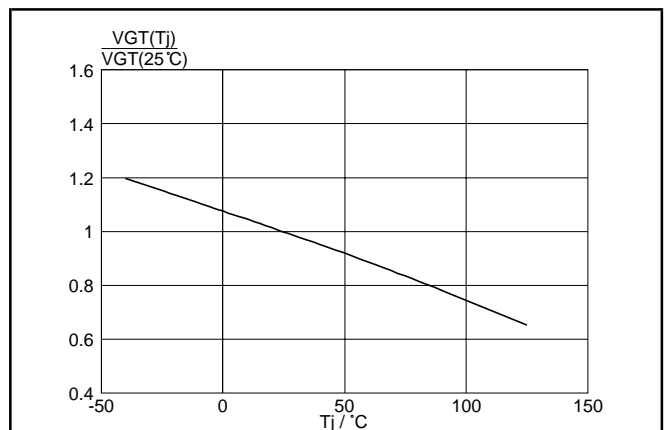
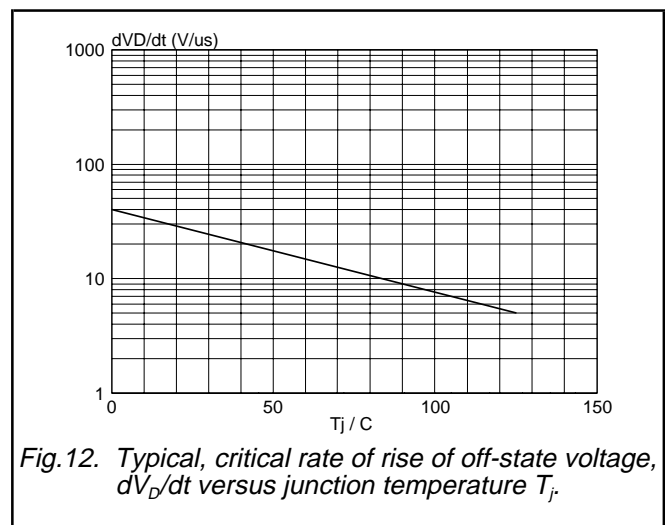
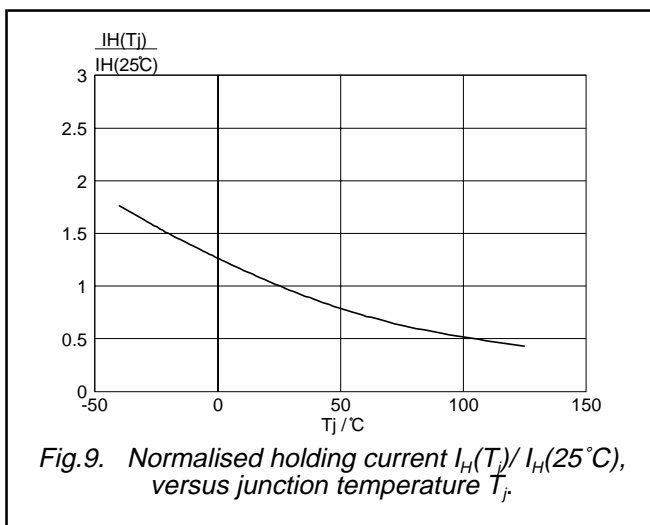
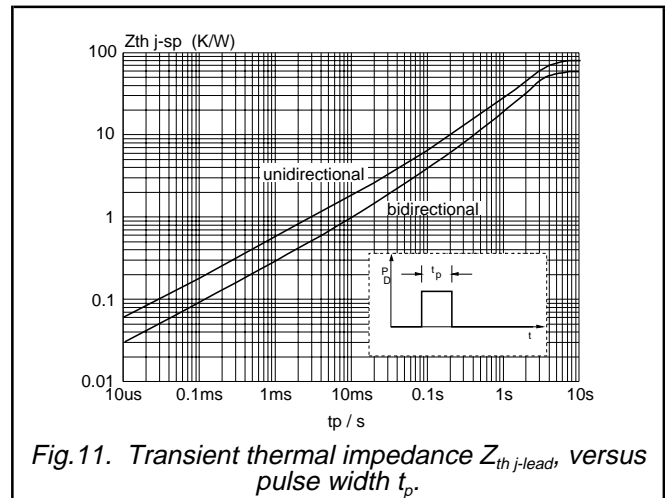
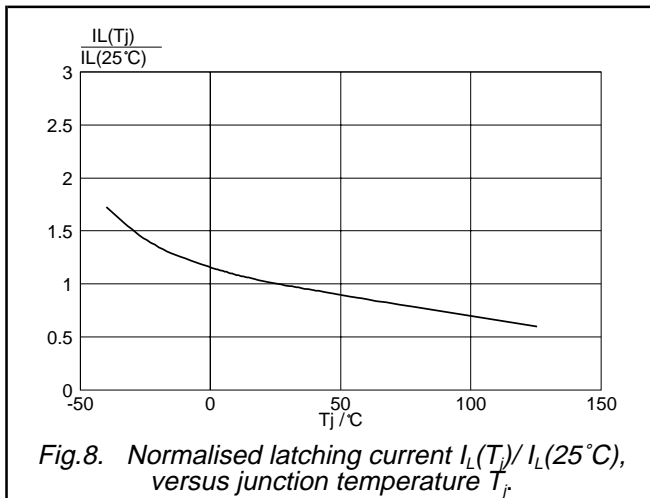
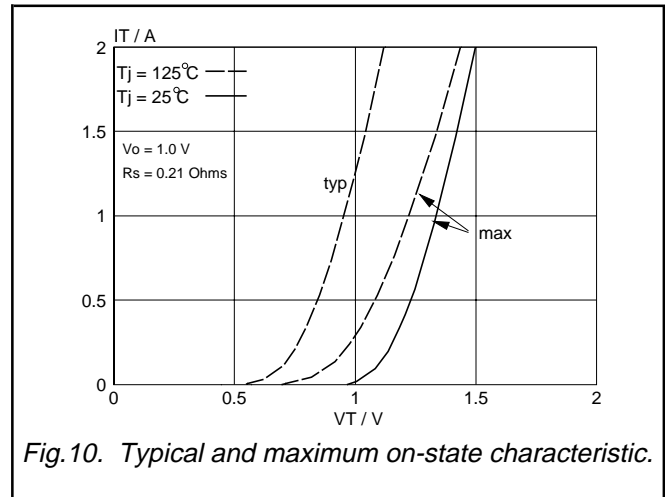
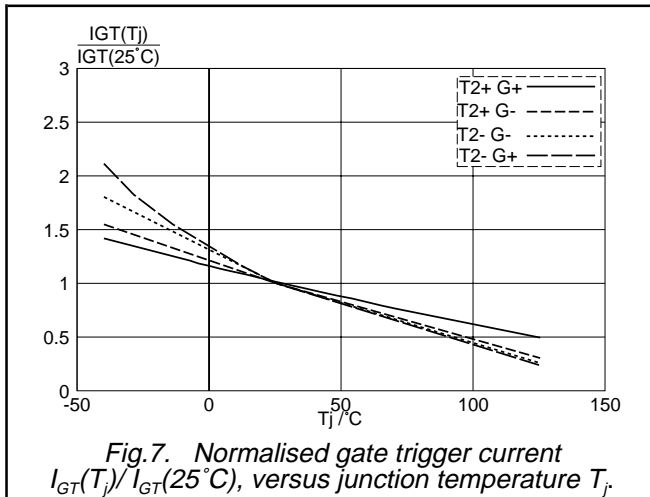


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .



MECHANICAL DATA

Dimensions in mm

Net Mass: 0.2 g

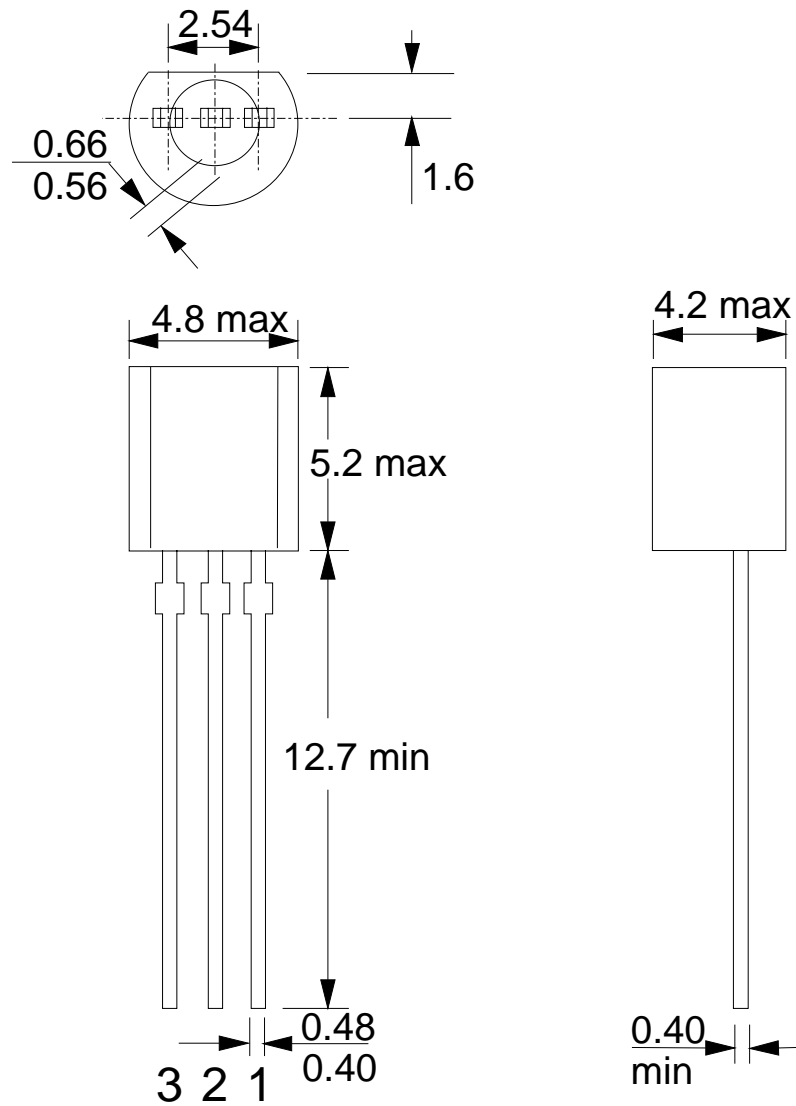


Fig.13. TO92 ; plastic envelope.

Notes

1. Epoxy meets UL94 V0 at 1/8".